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PN - JP5129226 A 19930525  
PD - 1993-05-25  
PR - JP19910287773 19911101  
OPD - 1991-11-01  
TI - MANUFACTURE OF SEMICONDUCTOR DEVICE  
IN - EGUCHI YOSHIKAZU  
PA - SEIKO EPSON CORP  
IC - H01L21/28 ; H01L21/285 ; H01L21/3205 ; H01L21/90

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TI - Forming wiring for semiconductor device - includes oxidising refractory metal silicide on semiconductor substrate before forming interlayer insulating film, tungsten@ filled contact hole, and aluminium@ wiring NoAbstract  
PR - JP19910287773 19911101  
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AB - PURPOSE: To realize good burying inside a contact hole by a metal by forming a good barrier metal in a wiring formation process of a semiconductor device.  
- CONSTITUTION: A high melting point metal silicide 103 is formed on a semiconductor substrate 101 and an oxide layer 104 which becomes a barrier metal is further formed by exposing it to oxygen plasma. Thereafter, layer insulating film 108 and a contact hole 105 are formed and a tungsten film 107 is deposited by sputtering method as an adherent layer, and a tungsten film 108 is deposited through chemical vapor reaction method. After tungsten in a region inside and outside of the contact hole is removed, an aluminum

none

none

none

copper/alloy film 109 is deposited and a wiring is completed by patterning.

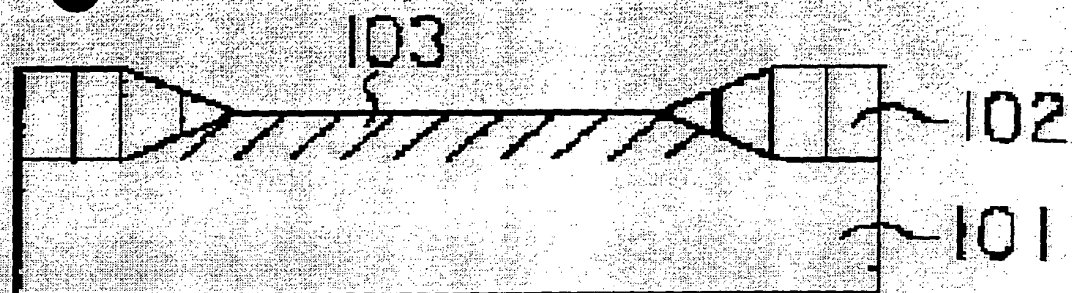
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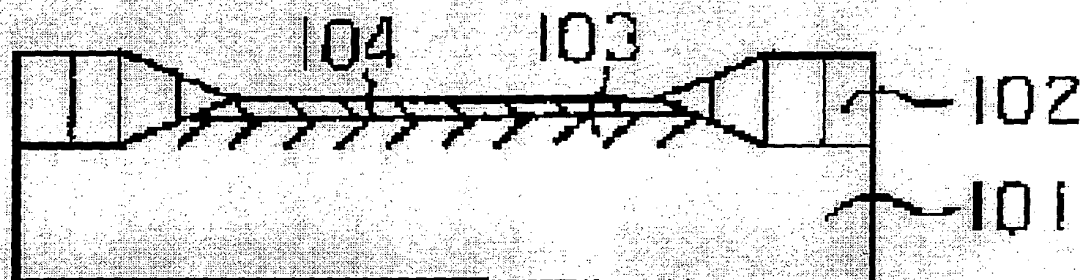
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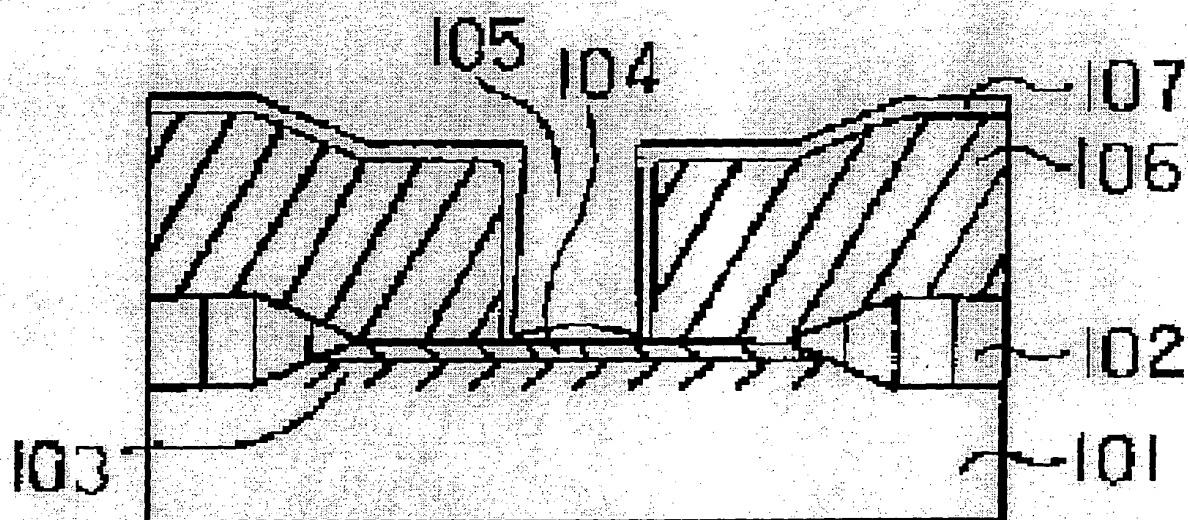
(a)



(b)



(c)



(d)

